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Vishay Siliconix

Automotive N-Channel 250 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	250				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0300				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 7.5 \text{ V}$	0.0320				
I _D (A)	65				
Configuration	Single				
Package	TO-263				

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



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N-Channel MOSFET	o S

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	Drain-source voltage		250	V	
Gate-source voltage		V_{GS}	± 20	V	
Continuous drain current	T _C = 25 °C	1	65		
Continuous drain current	T _C = 125 °C	l _D	37		
Continuous source current (diode conduction) a	Is	120	А		
Pulsed drain current ^b	I _{DM}	180			
Single pulse avalanche current		I _{AS}		41	
Single pulse avalanche energy	Single pulse avalanche energy		84	mJ	
Maximum power dissipation ^b	T _C = 25 °C	= 25 °C	375	W	
iviaximum power dissipation =	T _C = 125 °C	P_D	125	VV	
Operating junction and storage temperature rang	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient PCB mount ^c		R_{thJA}	40	°C/W	
Junction-to-case (drain)		R_{thJC}	0.4	C/VV	

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		250	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		3.0	3.5	V	
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 250 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 250 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 250 V, T _J = 175 °C	-	-	600	1	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 15 A	-	0.0244	0.0300		
Duning any una para state una interna a	Б	V _{GS} = 7.5 V	I _D = 10 A	-	0.0260	0.0320		
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.0650	Ω	
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.0868	1	
Forward transconductance b	9 _{fs}	V _{DS}	V _{DS} = 15 V, I _D = 15 A		50	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	2880	4050	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	1480	2100		
Reverse transfer capacitance	C _{rss}	1		-	58	85		
Total gate charge ^c	Qg			-	50	75		
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{GS} = 10 \text{ V}$ $V_{DS} = 125 \text{ V}, I_{D} = 10 \text{ A}$		12	-	nC	
Gate-drain charge ^c	Q _{gd}	1		-	15	-		
Gate Resistance	R_{g}	f = 1 MHz		1.40	2.84	4.40	Ω	
Turn-on delay time ^c	t _{d(on)}			-	14	30		
Rise time ^c	t _r	$V_{DD} =$	125 V, R_L = 12.5 $Ω$	-	6	15		
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10 A$,	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		38	60	ns	
Fall time ^c	t _f			-	10	20		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed current ^a	I _{SM}			-	-	180	Α	
Forward voltage	V _{SD}	I _F =	I _F = 20 A, V _{GS} = 0 V		0.82	1.5	V	
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs		-	155	260	ns	
Body diode reverse recovery charge	Q _{rr}			-	933	1400	nC	
Reverse recovery fall time	t _a			-	122	-	ns	
Reverse recovery rise time	t _b	7	-	33	-			
Body diode peak reverse recovery current	I _{RM(REC)}		-	-11.6	-	Α		

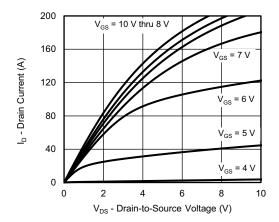
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

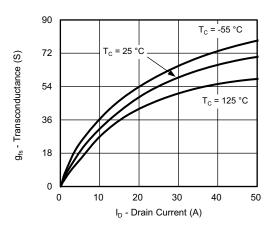
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



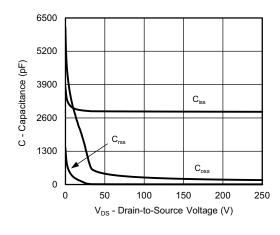
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



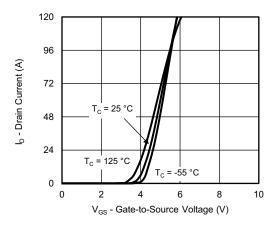
Output Characteristics



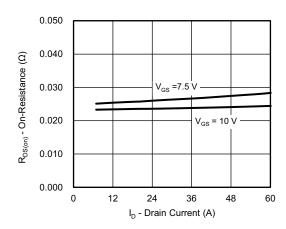
Transconductance



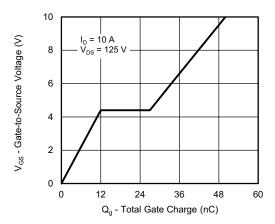
Capacitance



Transfer Characteristics



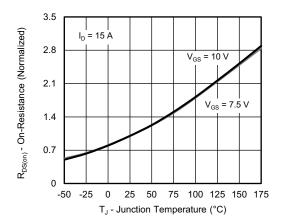
On-Resistance vs. Drain Current



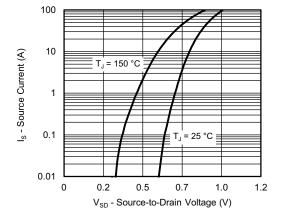
Gate Charge



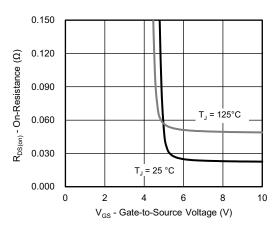
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



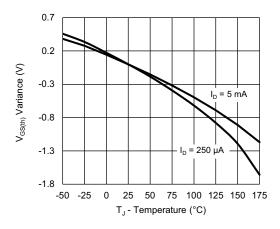
On-Resistance vs. Junction Temperature



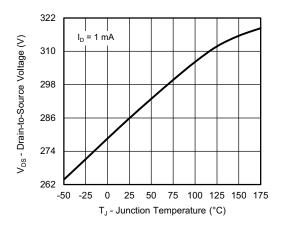
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



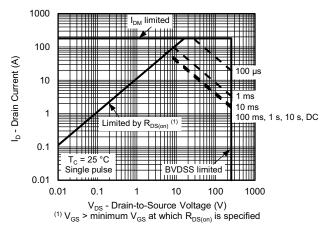
Threshold Voltage



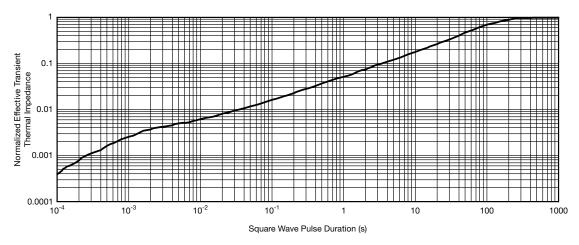
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



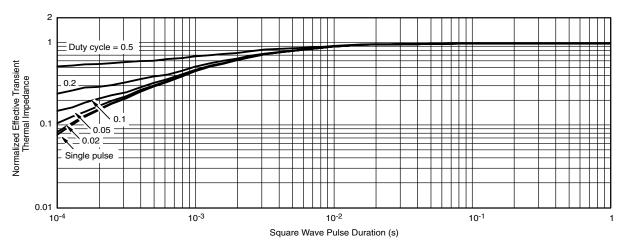
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

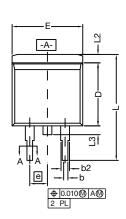
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

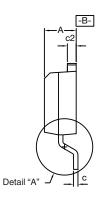
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

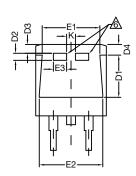
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TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



_ 1	b	
27	ਹ <i>ੀ </i>	
c	SECTION A-4	1

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

	INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	Е	0.380	0.410	9.652	10.414
	E1	0.245	-	6.223	=
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100) BSC	2.54 BSC	
	K	0.045	0.055	1.143	1.397
	L	0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
	L4	0.010 BSC		0.254 BSC	
	М	-	0.002	-	0.050
ECN: T13-0707-Rev. K, 30-Sep-13					

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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